(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
16 June 2011 (16.06.2011)

PCT

(10) International Publication Number
WO 2011/071980 A2

(51) **International Patent Classification**:
H01L 21/3065 (2006.01)

(21) **International Application Number**:
PCT/US2010/059388

(22) **International Filing Date**:
8 December 2010 (08.12.2010)

(25) **Filing Language**: English

(26) **Publication Language**: English

(30) **Priority Data**:
12/636,582 11 December 2009 (11.12.2009) US

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(81) **Designated States** *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) **Designated States** *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK,

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(54) **Title**: ULTRA LOW SILICON LOSS HIGH DOSE IMPLANT STRIP

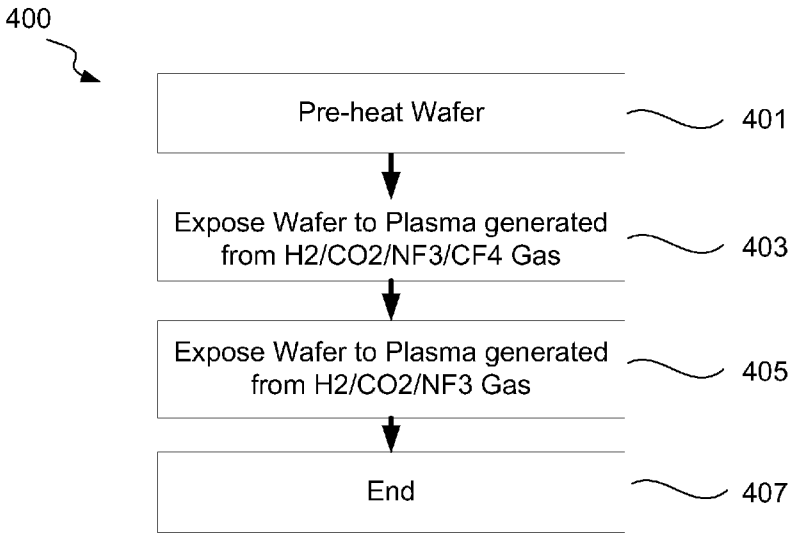


FIG. 4

(57) **Abstract**: Improved methods for stripping photoresist and removing ion implant related residues from a work piece surface are provided. According to various embodiments, plasma is generated using elemental hydrogen, a fluorine-containing gas and a protectant gas. The plasma-activated gases reacts with the high-dose implant resist, removing both the crust and bulk resist layers, while simultaneously protecting exposed portions of the work piece surface. The work piece surface is substantially residue free with low silicon loss.

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SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

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